

### THE DMN5L06WK IS NOT RECOMMENDED FOR NEW DESIGNS. PLEASE USE THE DMN52D0UW.



DMN5L06WK

### N-CHANNEL ENHANCEMENT MODE MOSFET

### **Features**

- Low On-Resistance
- Very Low Gate Threshold Voltage (1.0V max)
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected up to 2kV
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.

https://www.diodes.com/quality/product-definitions/

An automotive-compliant part is available under separate datasheet (DMN5L06WKQ)

### **Mechanical Data**

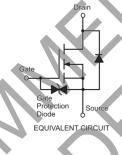
- Package: SOT-323
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin annealed over Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Terminal Connections: See Diagram
- Weight: 0.006 grams (Approximate)

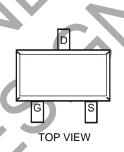




**TOP VIEW** 

SOT-323





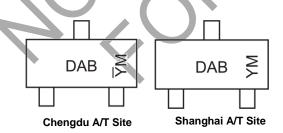
### **Ordering Information** (Note 4)

Part Number	Package		Pac	king
Part Number		Раскаде	Qty.	Carrier
DMN5L06WK-7		SOT-323	3000	Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

## **Marking Information**



DAB = Product Type Marking Code

YM = Date Code Marking for SAT (Shanghai Assembly/Test site) YM = Date Code Marking for CAT (Chengdu Assembly/Test site)

Y or  $\overline{Y}$  = Year (ex: L = 2024)

M = Month (ex: 5 = May)

### Date Code Key

Date Code Key												
Year	2006		2024	2025	2026	2027	2028	2029	2030	2031	2032	2033
Code	T		L	М	Ν	Р	R	S	Т	J	V	W
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec



# **Maximum Ratings** (@ $T_A = +25$ °C, unless otherwise specified.)

	Characteristic	Symbol	Value	Unit
Drain Source Voltage		VDSS	50	V
Gate-Source Voltage		$V_{GSS}$	±20	V
Drain Current (Note 5)	Continuous	1-	300	mA
	Pulsed (Note 6)	ID	800	IIIA

## Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

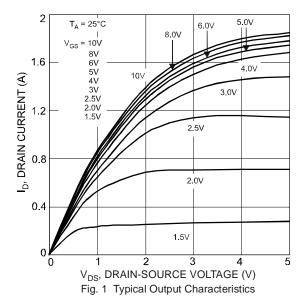
Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P <sub>D</sub>	250	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	500	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-65 to +150	°C

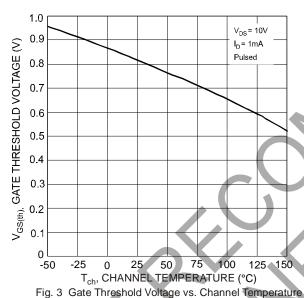
## **Electrical Characteristics** (@TA = +25°C, unless otherwise specified.)

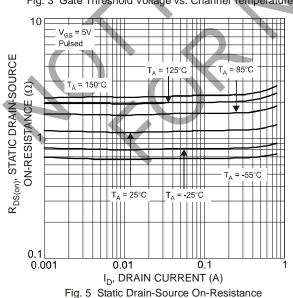
Chavastaviatia		Cumbal	Min	T.u.	Mari	1164	Toot Condition
Characteristic OFF CHARACTERISTICS (Note 7)		Symbol	Min	Тур	Max	Unit	Test Condition
Drain-Source Breakdown Voltage		BV <sub>DSS</sub>	50		_ 1	V	$V_{GS} = 0$ , $I_{D} = 10\mu A$
	「c = +25°C	IDSS	#	<b>V</b>	60	nA	$V_{DS} = 50V, V_{GS} = 0$
Gate-Body Leakage		Igss	1	-/	1 500 50	μΑ nA nA	$V_{GS} = \pm 12V, V_{DS} = 0$ $V_{GS} = \pm 10V, V_{DS} = 0$ $V_{GS} = \pm 5V, V_{DS} = 0$
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage		VGS(th)	0.49		1.0	V	$V_{DS} = V_{GS}$ , $I_D = 250 \mu A$
Static Drain-Source On-Resistance		RDS(on)		1	3.0 2.5 2.0	Ω	$V_{GS} = 1.8V, I_{D} = 50mA$ $V_{GS} = 2.5V, I_{D} = 50mA$ $V_{GS} = 5.0V, I_{D} = 50mA$
On-State Drain Current		I <sub>D</sub> (ON)	0.5	1.4	_	Α	Vgs = 10V, Vps = 7.5V
Forward Transconductance		Y <sub>fs</sub>	200	_	_	mS	$V_{DS} = 10V, I_{D} = 0.2A$
Source-Drain Diode Forward Voltage		$V_{SD}$	0.5		1.4	V	$V_{GS} = 0$ , $I_{S} = 115mA$
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance		Ciss	<u> </u>	_	50	pF	\/ 05\/ \/ 0
Output Capacitance		Coss			25	pF	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0, f = 1.0MHz
Reverse Transfer Capacitance		Crss	_	_	5.0	pF	1 = 1.0IVII IZ
Turn-On Delay Time		tD(on)	_	2.1	_	ns	
Turn-On Rise Time		tr	_	1.8	_	ns	V <sub>DD</sub> = 30V, V <sub>GS</sub> = 10V,
Turn-Off Delay Time		t <sub>D(off)</sub>	_	14.4	_	ns	$R_G = 25\Omega$ , $I_D = 200mA$
Turn-Off Fall Time		tf	_	8.4	_	ns	

- 5. Device mounted on FR-4 PCB.
  6. Pulse width ≤ 10µs, Duty Cycle ≤ 1%.
  7. Short duration pulse test used to minimize self-heating effect.
  8. Guaranteed by design. Not subject to production testing.

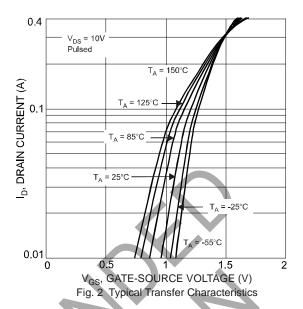








vs. Drain Current



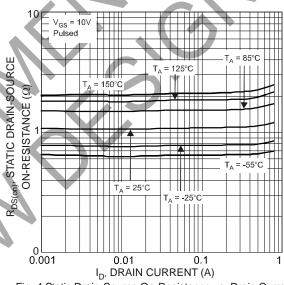


Fig. 4 Static Drain-Source On-Resistance vs. Drain Current

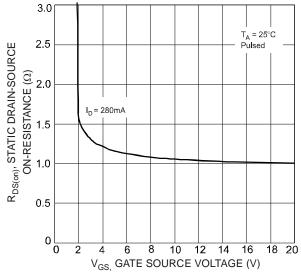


Fig. 6 Static Drain-Source On-Resistance vs. Gate-Source Voltage



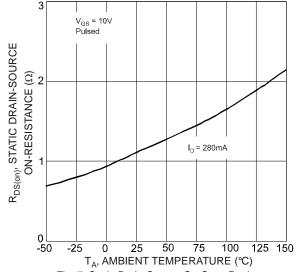


Fig. 7 Static Drain-Source On-State Resistance vs. Ambient Temperature

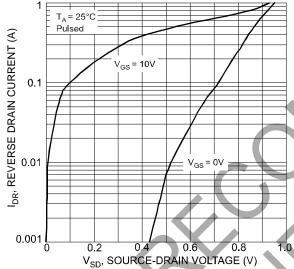
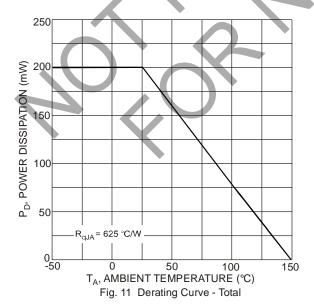


Fig. 9 Reverse Drain Current vs. Source-Drain Voltage



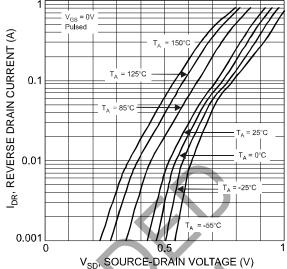


Fig. 8 Reverse Drain Current vs. Source-Drain Voltage

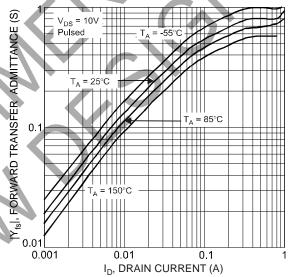


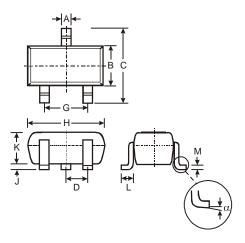
Fig.10 Forward Transfer Admittance vs. Drain Current



## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### **SOT-323**

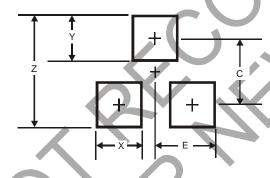


	SOT-323							
Dim	Min	Max	Тур					
Α	0.25	0.40	0.30					
В	1.15	1.35	1.30					
С	2.00	2.20	2.10 <					
D	-	-	0.65					
G	1.20	1.40	1.30					
Н	1.80	2.20	2.15					
J	0.0	0.10	0.05					
K	0.90	1.00	0.95					
L	0.25	0.40	0.30					
М	0.10	0.18	0.11					
α	_0°	8°	-					
All Dimensions in mm								

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT-323



Dimensions	Value (in mm)
Z	2.8
Х	0.7
Υ	0.9
С	1.9
	4 0

May 2024



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